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(54) Title: SEMICONDUCTOR CONSTRUCTIONS AND TRANSISTORS, AND METHODS OF FORMING SEMICONDUCTOR CONSTRUCTIONS AND TRANSISTORS

(57) Abstract: The invention includes a transistor device having a semiconductor substrate with an upper surface. A pair of source/drain regions are formed within the semiconductor substrate and a channel region is formed within the semiconductor substrate and extends generally perpendicularly relative to the upper surface of the semiconductor substrate. A gate is formed within the semiconductor substrate between the pair of the source/drain regions.